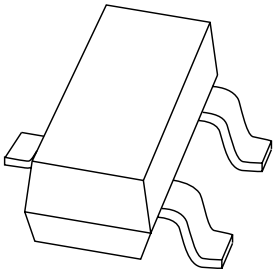
DATA SHEET



PMBT2222; PMBT2222A
NPN switching transistors

Product data sheet
Supersedes data of 1999 Apr 27

2004 Jan 22

NPN switching transistors

PMBT2222; PMBT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.
PNP complements: PMBT2907 and PMBT2907A.

MARKING

TYPE NUMBER	MARKING CODE(1)
PMBT2222	*1B
PMBT2222A	*1P

Note

1. * = p : Made in Hong Kong.
   * = t : Made in Malaysia.
   * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

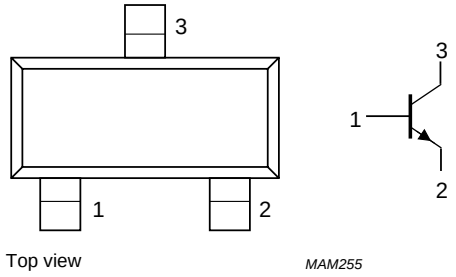


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT2222	–	plastic surface mounted package; 3 leads	SOT23
PMBT2222A			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	PMBT2222		–	60	V
	PMBT2222A		–	75	V
V_{CEO}	collector-emitter voltage	open base			
	PMBT2222		–	30	V
	PMBT2222A		–	40	V
V_{EBO}	emitter-base voltage	open collector			
	PMBT2222		–	5	V
	PMBT2222A		–	6	V
I_C	collector current (DC)		–	600	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

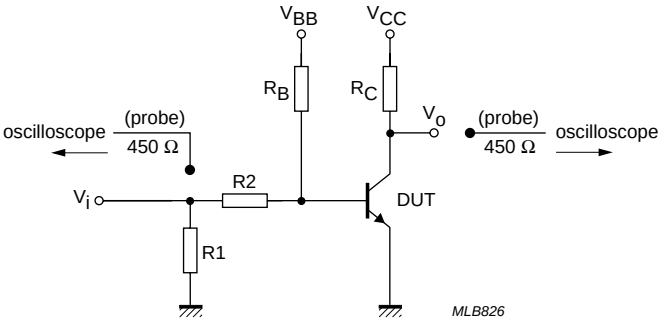
$T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current				
	PMBT2222	$I_E = 0$; $V_{CB} = 50$ V	–	10	nA
		$I_E = 0$; $V_{CB} = 50$ V; $T_j = 125$ °C	–	10	μA
	collector cut-off current				
	PMBT2222A	$I_E = 0$; $V_{CB} = 60$ V	–	10	nA
		$I_E = 0$; $V_{CB} = 60$ V; $T_j = 125$ °C	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5$ V			
	PMBT2222A		–	10	nA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
h_{FE}	DC current gain	I_C = 0.1 mA; V_{CE} = 10 V	35	–	
		I_C = 1 mA; V_{CE} = 10 V	50	–	
		I_C = 10 mA; V_{CE} = 10 V	75	–	
		I_C = 10 mA; V_{CE} = 10 V; T_{amb} = −55 °C	35	–	
		I_C = 150 mA; V_{CE} = 10 V	100	300	
		I_C = 150 mA; V_{CE} = 1 V	50	–	
	DC current gain	I_C = 500 mA; V_{CE} = 10 V			
	PMBT2222		30	–	
	PMBT2222A		40	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA; note 1			
	PMBT2222		–	400	mV
	PMBT2222A		–	300	mV
	collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; note 1			
	PMBT2222		–	1.6	V
	PMBT2222A		–	1	V
V_{BEsat}	base-emitter saturation voltage	I_C = 150 mA; I_B = 15 mA; note 1			
	PMBT2222		–	1.3	V
	PMBT2222A		0.6	1.2	V
	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; note 1			
	PMBT2222		–	2.6	V
	PMBT2222A		–	2	V
C_c	collector capacitance	$I_E = I_e$ = 0; V_{CB} = 10 V; f = 1 MHz	–	8	pF
C_e	emitter capacitance	$I_C = I_c$ = 0; V_{EB} = 500 mV; f = 1 MHz			
	PMBT2222		–	30	pF
	PMBT2222A		–	25	pF
f_T	transition frequency	I_C = 20 mA; V_{CE} = 20 V; f = 100 MHz			
	PMBT2222		250	–	MHz
	PMBT2222A		300	–	MHz
F	noise figure	I_C = 100 μA; V_{CE} = 5 V; R_S = 1 kΩ; f = 1 kHz	–	4	dB
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	I_{Con} = 150 mA; I_{Bon} = 15 mA; I_{Boff} = −15 mA	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

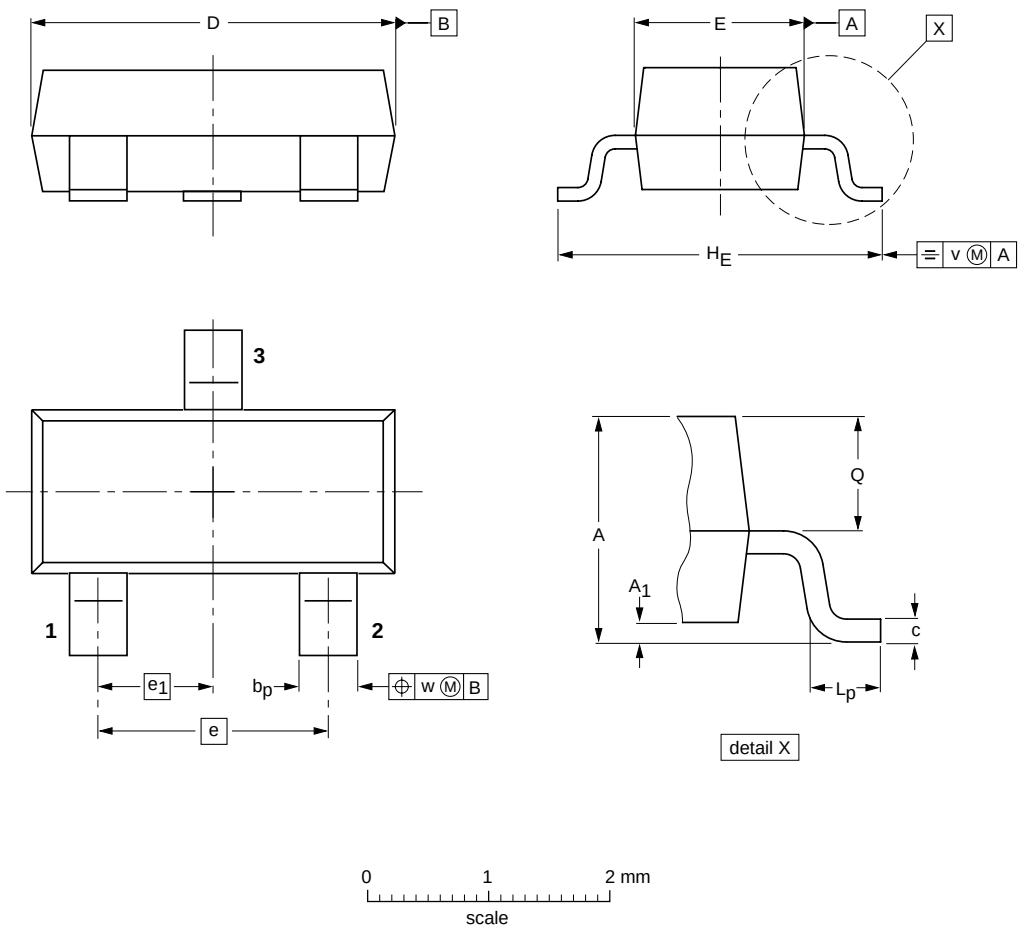


V_i = 9.5 V; T = 500 μs; t_p = 10 μs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = −3.5 V; V_{CC} = 29.5 V.
Oscilloscope: input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				~~04-11-04~~ 06-03-16

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: **http://www.nxp.com**
For sales offices addresses send e-mail to: **salesaddresses@nxp.com**

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